TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L57AE

VHF~UHF Band Low Noise Amplifier Applications

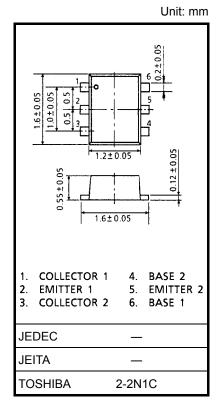
• Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

Mounted Devices

| | Q1: SSM (TESM) | Q2: SSM (TESM) |
|--|----------------|----------------|
| Three-pins (SSM/TESM) mold products are corresponded. | MT3S06S | MT3S04AS |
| | (MT3S06T) | (MT3S04AT) |

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Q1 | Q2 | Unit |
|-----------------------------|----------------------------|---------|----|------|
| Collector-base voltage | V _{CBO} | 10 | 10 | V |
| Collector-emitter voltage | V _{CEO} | 5 | 5 | V |
| Emitter-base voltage | V _{EBO} | 1.5 | 2 | V |
| Collector current | Ι _C | 15 | 40 | mA |
| Base current | Ι _Β | 7 | 10 | mA |
| Collector power dissipation | P _C (Note 1) | 100 | | mW |
| Junction temperature | Tj | 125 | | °C |
| Storage temperature range | T _{stg} | -55~125 | | °C |



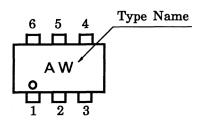
Weight: 0.003 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

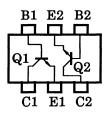
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total power dissipation of Q1 and Q2.

Marking



Pin Assignment (top view)



Electrical Characteristics Q1 (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------------|-------------------------------------|---|-----|------|------|------|
| Collector cut-off current | I _{CBO} | $V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$ | _ | _ | 0.1 | μA |
| Emitter cut-off current | I _{EBO} | $V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$ | — | | 1 | μA |
| DC current gain | h _{FE} | $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$ | 70 | _ | 140 | |
| Transition frequency | f _T | $V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$ | 7 | 10 | | GHz |
| Insertion gain | S _{21e} ² (1) | $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | _ | 7.5 | | dB |
| | S _{21e} ² (2) | $V_{CE} = 3 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | 4.5 | 8 | | |
| Noise figure | NF (1) | $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | _ | 1.7 | 3 | dB |
| | NF (2) | $V_{CE} = 3 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | _ | 1.6 | 3 | чв |
| Reverse transfer capacitance | C _{re} | $V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note 2) | _ | 0.35 | 0.75 | pF |

Note 2: Cre is measured by 3 terminal method with capacitance bridge.

Electrical Characteristics Q2 (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|------------------------------|-------------------------------------|---|-----|------|------|------|--|
| Collector cut-off current | I _{CBO} | $V_{CB} = 5 V, I_E = 0$ | _ | _ | 0.1 | μA | |
| Emitter cut-off current | I _{EBO} | $V_{EB} = 1 V, I_{C} = 0$ | _ | _ | 1 | μA | |
| DC current gain | h _{FE} | $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$ | 80 | _ | 160 | | |
| Transition frequency | f _T (1) | $V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$ | 2 | 4.5 | _ | GHz | |
| | f _T (2) | $V_{CE} = 3 \text{ V}, \text{ I}_{C} = 7 \text{ mA}$ | 5 | 7 | _ | | |
| Insertion gain | S _{21e} ² (1) | $V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 1 \text{ GHz}$ | _ | 8.5 | _ | dB | |
| | S _{21e} ² (2) | V_{CE} = 3 V, I _C = 20 mA, f = 1 GHz | 7.5 | 11 | _ | ub | |
| Noise figure | NF (1) | $V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 1 \text{ GHz}$ | _ | 1.3 | 2.2 | dB | |
| | NF (2) | $V_{CE} = 3 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 1 \text{ GHz}$ | _ | 1.2 | 2 | | |
| Reverse transfer capacitance | C _{re} | $V_{CB}=1~V,~I_{E}=0,~f=1~MHz \qquad (Note~2)$ | _ | 0.9 | 1.25 | pF | |

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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20070701-EN GENERAL

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